

2SC1518

Silicon NPN epitaxial planer type

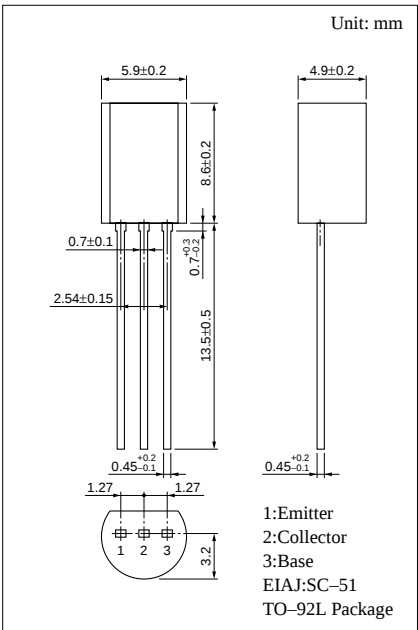
For high-frequency bias oscillation of tape recorders
For DC-DC converter

■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Satisfactory operation performances and high efficiency with a low-voltage power supply.

■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1.5	A
Collector current	I_C	1	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C



■ Electrical Characteristics (Ta=25°C)

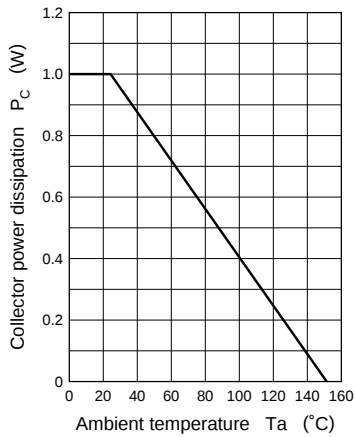
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 25V, I_E = 0$			100	nA
	I_{CEO}	$V_{CE} = 20V, I_B = 0$			1	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu A, I_E = 0$	25			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	20			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = 2V, I_C = 500mA^{*2}$	90		330	
	h_{FE2}	$V_{CE} = 2V, I_C = 1A^{*2}$	50	100		
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA^{*2}$			1.2	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 50mA^{*2}$			0.5	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		12	20	pF

^{*2} Pulse measurement

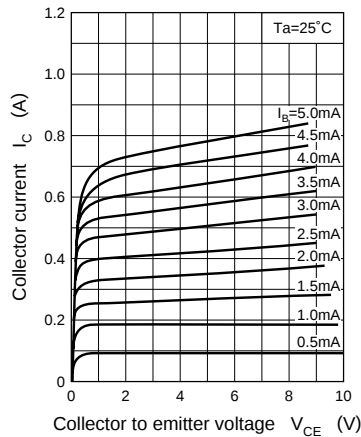
^{*1} h_{FE1} Rank classification

Rank	Q	R	S
h_{FE1}	90 ~ 155	130 ~ 220	185 ~ 330

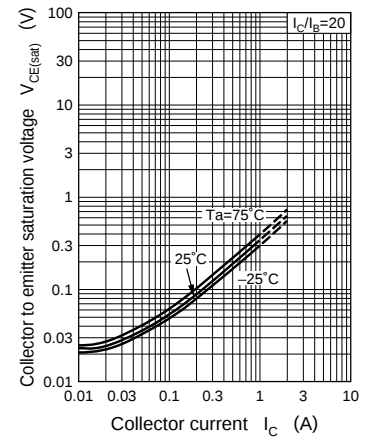
$P_C - T_a$



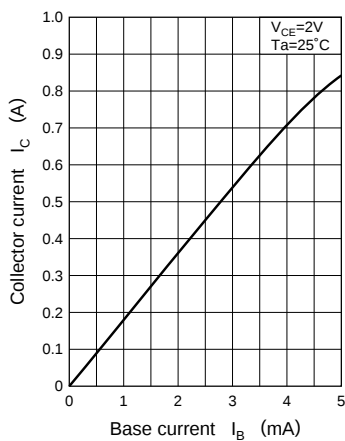
$I_C - V_{CE}$



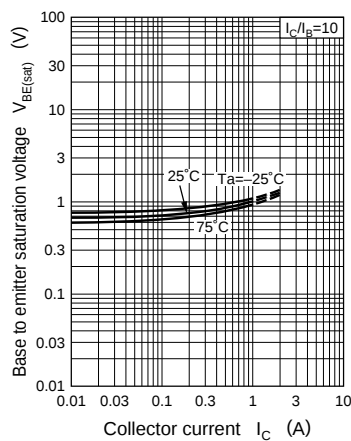
$V_{CE(sat)} - I_C$



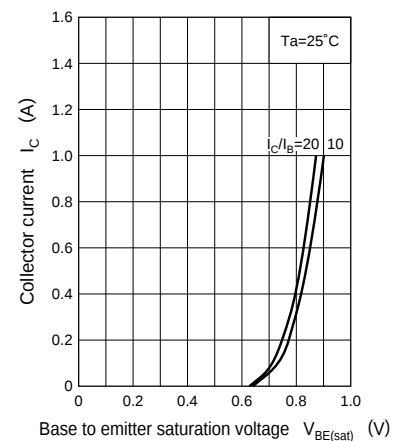
$I_C - I_B$



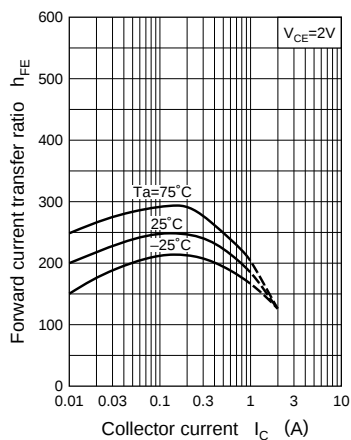
$V_{BE(sat)} - I_C$



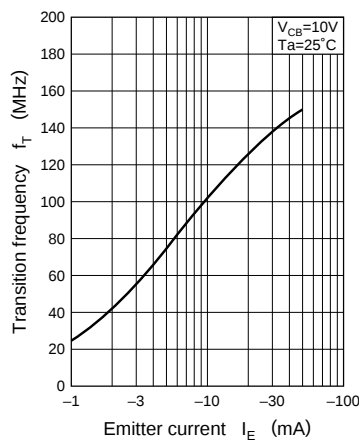
$I_C - V_{BE(sat)}$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

